

Ultra-Low Capacitance TVS Protection

◆ DESCRIPTIONS

CMTLDF02C1R8AFE is a low-capacitance Transient Voltage Suppressor (TVS) designed to provide electrostatic discharge (ESD) protection for high-speed data interfaces. With typical capacitance of 0.35pF only, CMTLDF02C1R8AFE is designed to protect parasitic-sensitive systems against over-voltage and over-current transient events. It complies with IEC 61000-4-2 (ESD), Level 4 ($\pm 15\text{kV}$ air, $\pm 8\text{kV}$ contact discharge), IEC 61000-4-4 (electrical fast transient - EFT) (40A, 5/50 ns), very fast charged device model (CDM) ESD and cable discharge event (CDE), etc.

CMTLDF02C1R8AFE uses ultra-small uDFN-2L package. Each CMTLDF02C1R8AFE device can protect one high-speed data line. It offers system designers flexibility to protect single data line where space is a premium concern. The combined features of low capacitance, ultra-small size and high ESD robustness make CMTLDF02C1R8AFE ideal for high-speed data port and high-frequency line (e.g., USB 2.0 & antenna line) applications, such as cellular phones and HD visual devices.

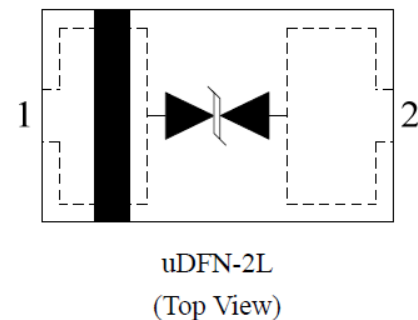
◆ FEATURES

- 1、Transient protection for high-speed data lines
IEC 61000-4-2 (ESD) $\pm 15\text{kV}$ (Air)
 $\pm 8\text{kV}$ (Contact)
IEC 61000-4-4 (EFT) 40A (5/50 ns)
Cable Discharge Event (CDE)
- 2、Package optimized for high-speed lines
- 3、Ultra-small package (1.0mm \times 0.6mm \times 0.4mm)
- 4、Protects one data, control or power line
- 5、Low capacitance: 1.8pF (Typical)
- 6、Low leakage current: 10nA @ V_{RWM} (Typical)
- 7、Low clamping voltage

◆ Circuit Diagram



◆ Pin Configuration



◆ Applications

- 1、10M / 100M / 1G Ethernet
- 2、PCI Express
- 3、PC / Note book
- 4、Cellular Phones
- 5、MDDI Ports
- 6、USB2.0 Power and Data Line Protection
- 7、Display Ports
- 8、HDMI/DVI ports

◆ Mechanical Characteristics

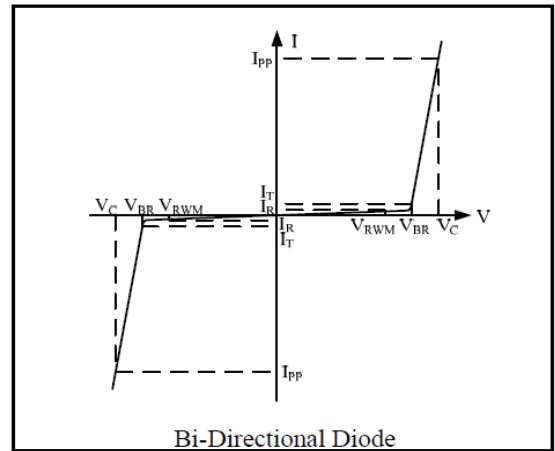
- 1、uDFN-2L package
- 2、Flammability Rating: UL 94V-0
- 3、Marking: Part number (S)
- 4、Packaging: Tape and Reel

◆ **Absolute Maximum Rating**

Symbol	Parameter	Value	Units
V_{ESD}	ESD per IEC 61000-4-2 (Air)	± 17	kV
	ESD per IEC 61000-4-2 (Contact)	± 12	
T_{OPT}	Operating Temperature	-55/+125	$^{\circ}C$
T_{STG}	Storage Temperature	-55/+150	$^{\circ}C$

◆ **Electrical Characteristics (T = 25 $^{\circ}C$)**

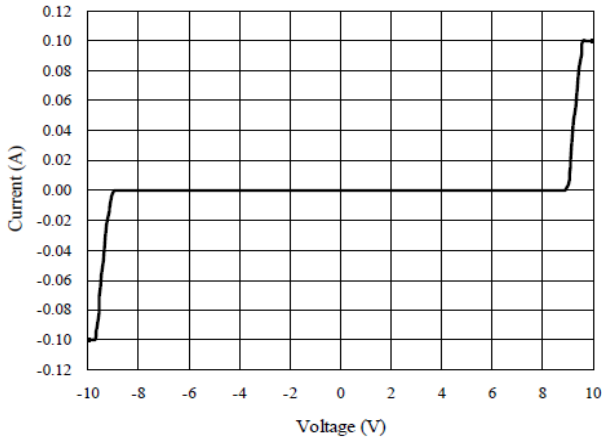
Symbol	Parameter
V_{RWM}	Nominal Reverse Working Voltage
I_R	Reverse Leakage Current @ V_{RWM}
V_{BR}	Reverse Breakdown Voltage @ I_T
I_T	Test Current for Reverse Breakdown
V_C	Clamping Voltage @ I_{PP}
I_{PP}	Peak Pulse Current
C_{ESD}	Parasitic Capacitance
V_R	Reverse Voltage
f	Small Signal Frequency



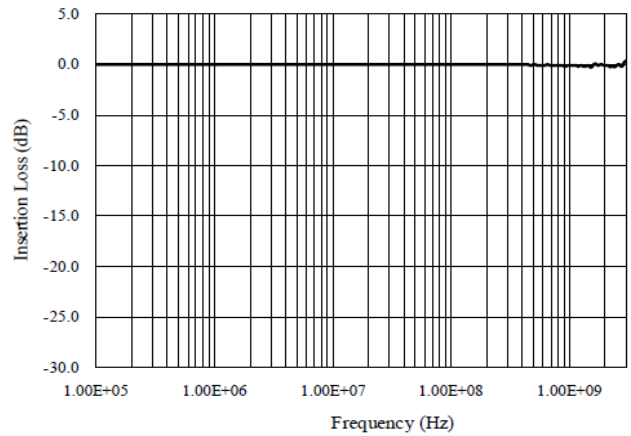
Symbol	Test Condition	Minimum	Typical	Maximum	Units
V_{RWM}				5.0	V
I_R	$V_{RWM} = 5V, T = 25^{\circ}C$ Between I/O and I/O		0.01	1.0	μA
V_{BR}	$I_T = 1mA$ Between I/O and I/O	6.0	8.8	11	V
V_C	$I_{PP} = 1A, t_p = 8/20\mu s$ Between I/O and I/O			12	V
V_C	$I_{PP} = 2A, t_p = 8/20\mu s$ Between I/O and I/O			14	V
C_{ESD}	$V_R = 0V, f = 1MHz$ Between I/O and I/O	1.0	1.8	2.5	pF

◆ TYPICAL ELECTRICAL CHARACTERISTICS CURVE

Voltage Sweeping of I/O to I/O

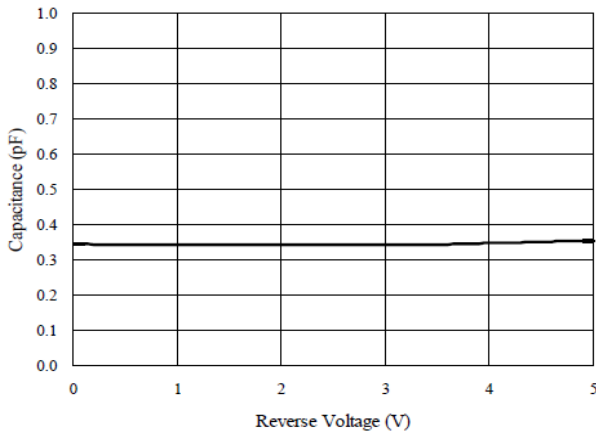


Insertion Loss S21 of I/O to I/O

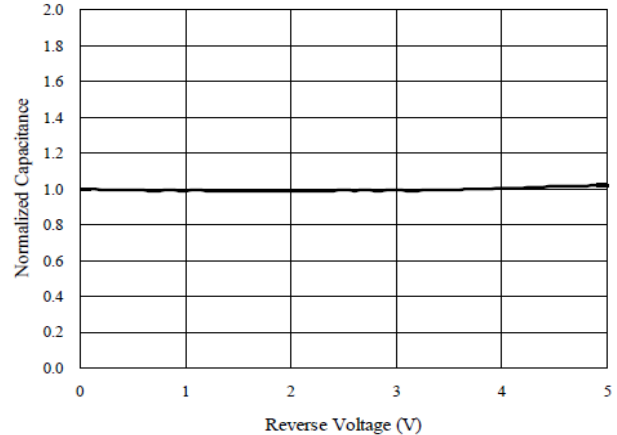


Capacitance vs. Voltage of I/O to I/O (f = 1MHz)

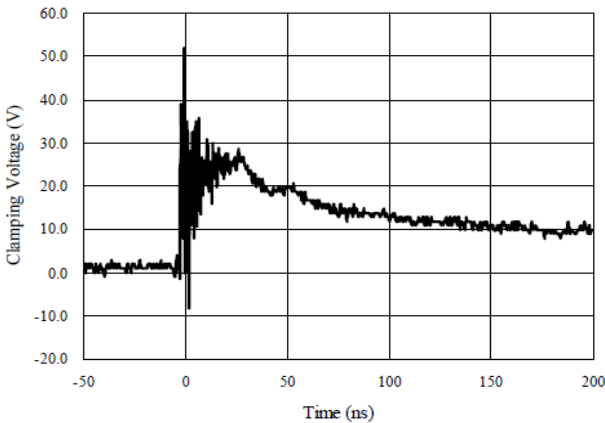
Capacitance vs. Reverse Voltage



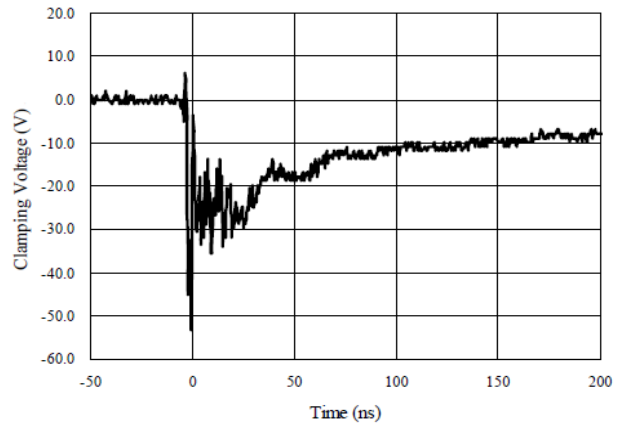
Normalized Capacitance vs. Reverse Voltage



ESD Clamping of I/O to I/O
(+8kV Contact per IEC 61000-4-2)

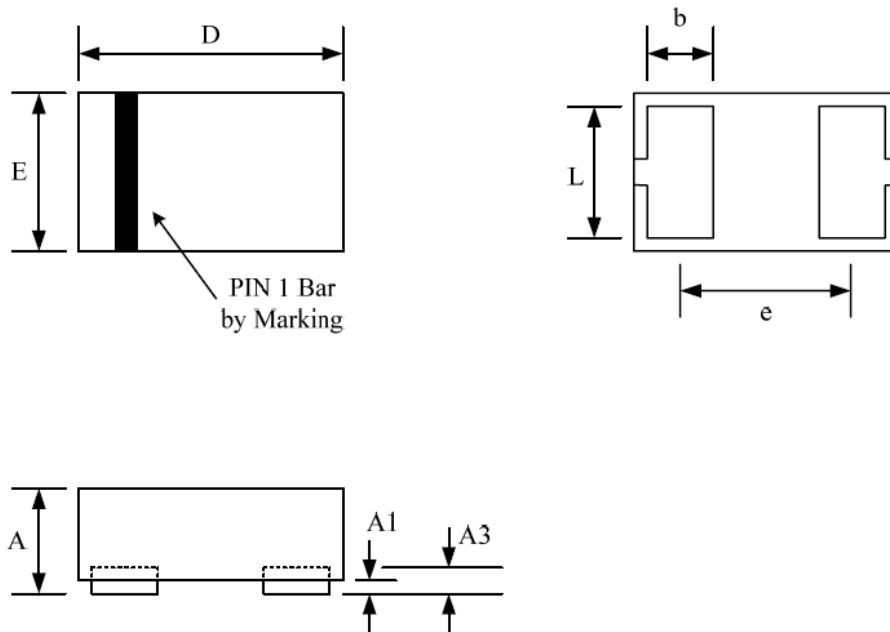


ESD Clamping of I/O to I/O
(-8kV Contact per IEC 61000-4-2)



◆ **PACKAGE OUTLINE**

- 1、 uDFN-2L package
- 2、 2 leads, very small package
- 3、 Thermally-Enhanced



Package Dimensions (Controlling dimensions are in millimeters)

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Minimum	Maximum	Minimum	Maximum
A	0.400	0.550	0.016	0.022
A1	0.000	0.050	0.000	0.002
A3	0.125 REF		0.005 REF	
D	0.950	1.050	0.037	0.041
E	0.550	0.650	0.022	0.026
b	0.200	0.300	0.008	0.012
e	0.650 BSC		0.026 BSC	
L	0.450	0.550	0.018	0.022